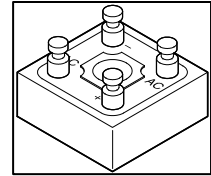


TECHNICAL DATA
DATA SHEET 2014, REV. B



THREE PHASE FULL WAVE BRIDGE RECTIFIER ASSEMBLY

DESCRIPTION: A 200/400/600 VOLT, 7.5 AMP, 180 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^\circ\text{C}$ unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV) S10A20FR S10A40FR S10A60FR	-	-	-	200 400 600	Vdc
Average DC Output Current (T_C = Case Temp) (I_o)	$T_C = 55^\circ\text{C}$ $T_C = 100^\circ\text{C}$ $T_C = 125^\circ\text{C}$	-	-	10 7.5 5.0	Amps
Average DC Output Current Ambient Temp. (no heat sink) (I_o)	$T_A = 25^\circ\text{C}$ $T_A = 55^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	4.0 3.0 2.0	Amps
Peak Single Cycle Surge Current (I_{FSM})	$t_p = 8.3$ ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	100	Amps(pk)
Peak Recurring Surge Current (I_{FRM})	$T_A = 25^\circ\text{C}$	-	-	50	Amps
Operating and Storage Temp. $(T_{op}$ & $T_{stg})$	-	-55	-	+150	$^\circ\text{C}$
Maximum Forward Voltage (V_f)	$I_f = 9.0\text{A}$ (300 μsec pulse, duty cycle < 2%)	-	-	1.6	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	2.0 100	μAmps
Reverse Recovery Time (t_{rr})	$I_f = 0.5\text{A}$, $I_r = 1.0\text{A}$, $I_{rr} =$ 0.25A	-	-	180	nsec
Thermal Resistance (θ_{JL})	-	-	-	2.0	$^\circ\text{C/W}$

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MECHANICAL DIMENSIONS: In Inches / mm

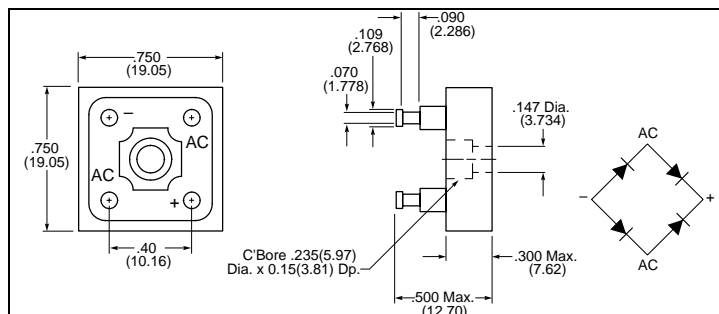


FIG. 401

Note: Case finish - Black Anodized

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